

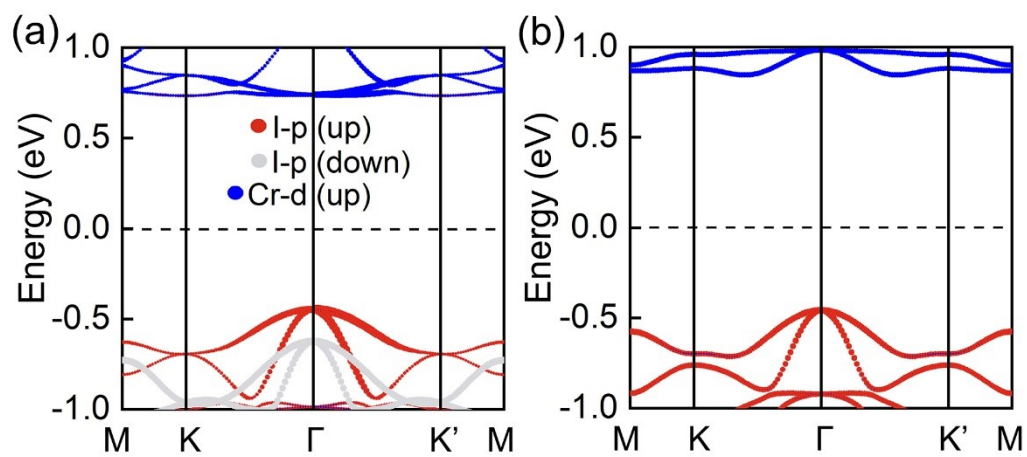
## Supplementary Information for

# Robust second-order topological insulator in 2D van der Waals magnet CrI<sub>3</sub>

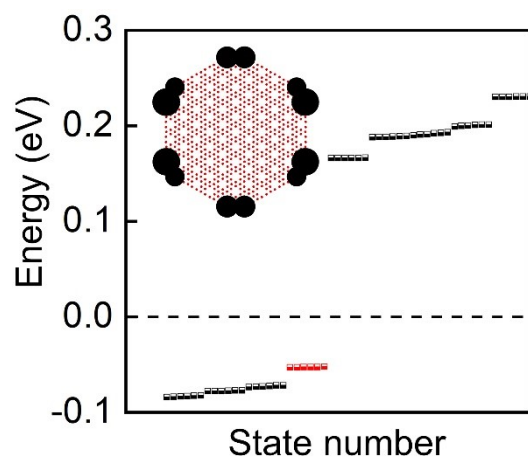
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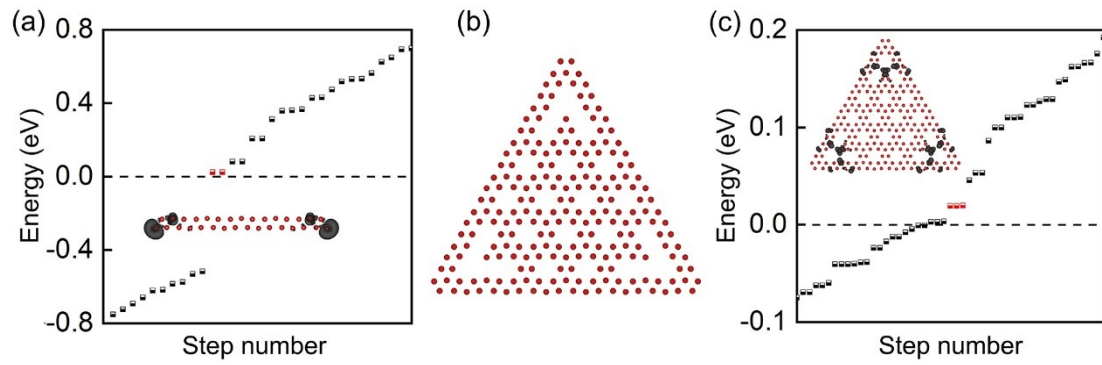
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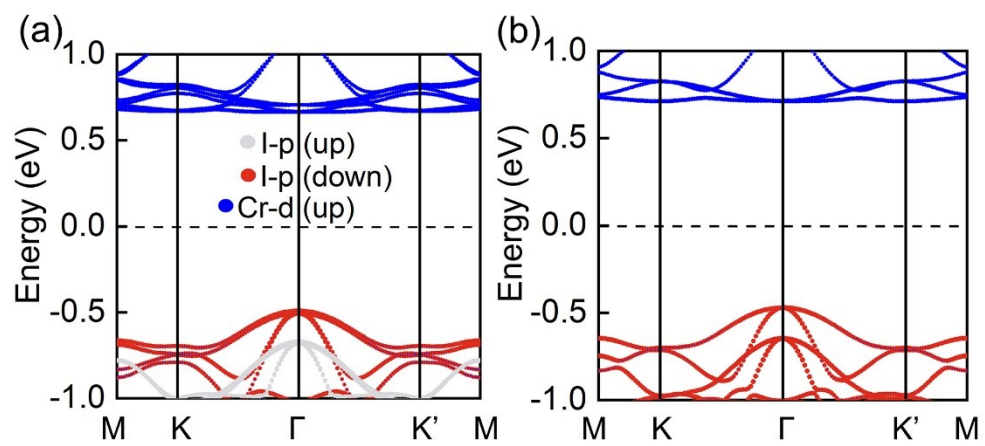
**Fig. S1** Band structures of CrI<sub>3</sub> monolayer without SOC for (a) FM ordering and (b) AFM ordering.



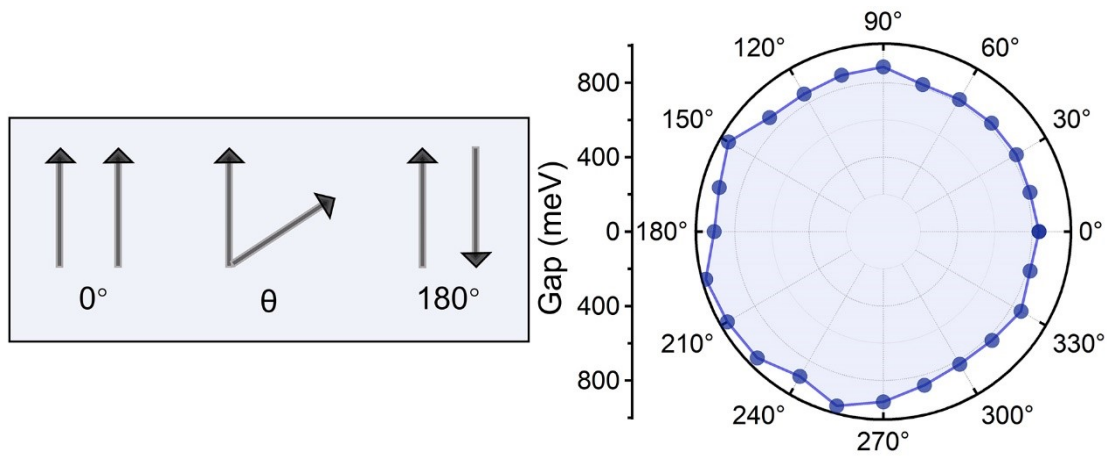
**Fig. S2** Energy discrete spectra of hexagonal nanoflake for FM CrI<sub>3</sub> monolayer. Insets show the total charge distribution of the six occupied corner states.



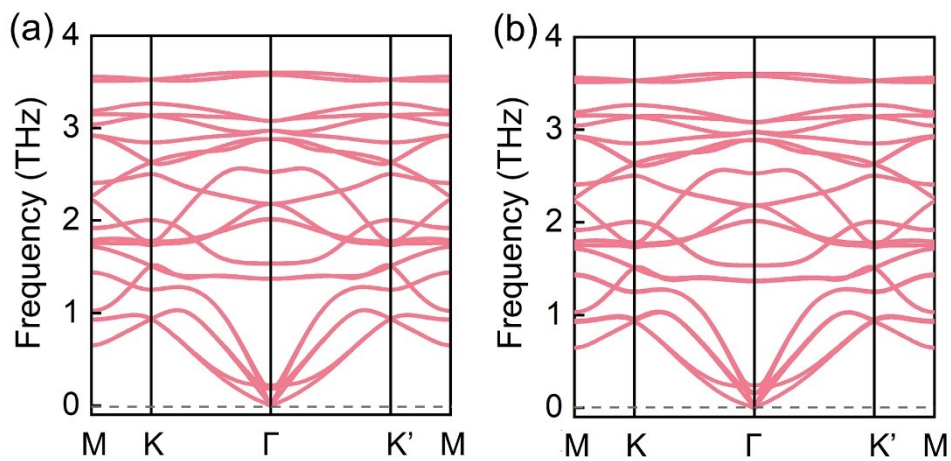
**Fig.S3** (a) Energy spectrum of the finite 1D nanostructure, exhibiting two topological end states. Inset is the charge density distribution of the topological end states. (b) Finite nanoflake of  $\text{CrI}_3$  containing three point-defects. (c) Energy spectrum of the finite nanoflake, showing the emergence of topological point states located inside the bulk band gap. Insets are charge density distributions of in-gap topological point states.



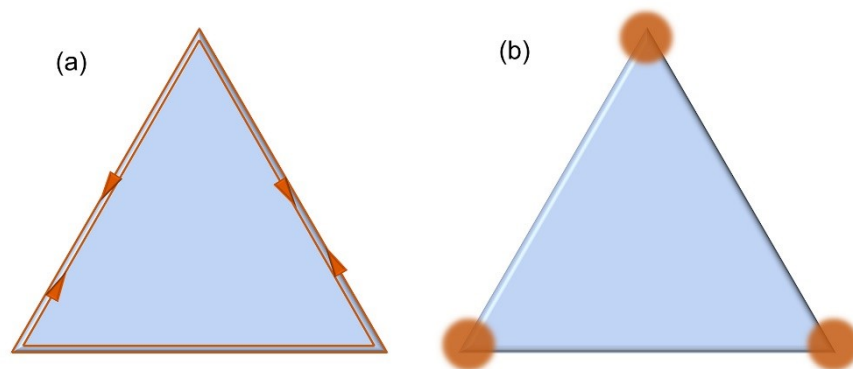
**Fig. S4** Band structures of CrI<sub>3</sub> bilayers without SOC for (a) AB stacking and (b) AB' stacking.



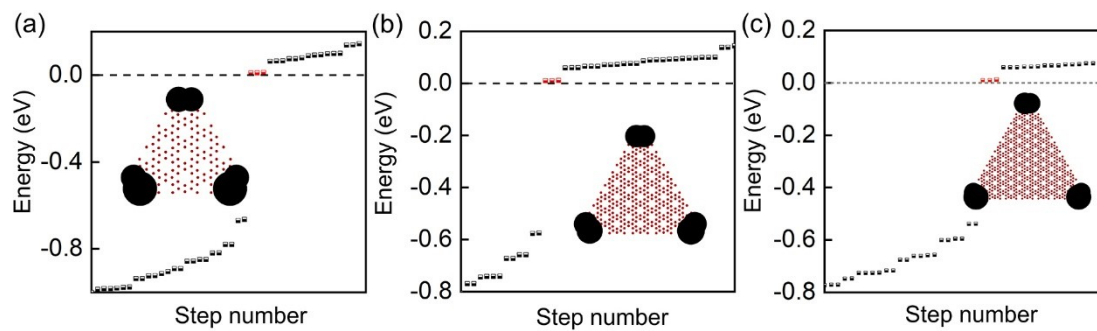
**Fig. S5** Evolution of the global band gaps for CrI<sub>3</sub> monolayer with respect to the relative spin orientations  $\theta$ . There is no band gap closing and reopening process, revealing the robustness of SOTIs against magnetic transition between FM ( $\theta = 0^\circ$ ) and AFM ( $\theta = 180^\circ$ ) orderings.



**Fig. S6** Phonon spectrums of  $\text{CrI}_3$  bilayers for (a) AB stacking and (b) AB' stacking. The absence of imagine frequency in the whole Brillouin zone indicates the dynamical stability.

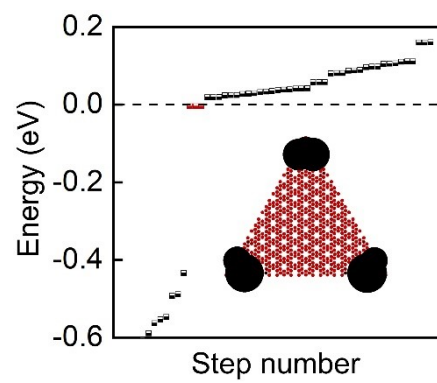


**Fig. S7** (a) The schematic of carrier transport for conventional two-dimensional topological insulators, where carriers with opposite spins propagate in opposite directions along the edges, forming helical edge states. (b) The localized carrier distribution of higher-order topological insulators, where the carriers are confined to specific geometric locations.





**Fig. S8** Energy discrete spectra of the triangular nanoflakes for AFM CrI<sub>3</sub> monolayer with (a) 8×8, (b) 12×12 and (c) 16×16 sizes, where the bulk and nontrivial corner states are marked by red and black dots, respectively. Insets show the total charge distribution of the three occupied corner states.



**Fig. S9** Energy discrete spectrum of a nanoflake for FM CrI<sub>3</sub> monolayer without spin-orbital coupling. Red dots represent the in-gap corner states. Insets show the total charge distributions of the corresponding corner states.